

SANYO

No.978B

2SC3067

NPN Epitaxial Planar Silicon Transistor

DIFFERENTIAL AMP APPLICATIONS

Features

- . Excellent in thermal equilibrium and suited for use in first-stage differential amp.
- . Low noise.
- . Matched pair capability.

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CB0}	130	V
Collector to Emitter Voltage	V _{CEO}	120	V
Emitter to Base Current	V _{EBO}	5	V
Collector Current	I _C	50	mA
Peak Collector Current	i _{cp}	100	mA
Collector Dissipation	P _C	200	mW
Total Dissipation	P _T	400	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

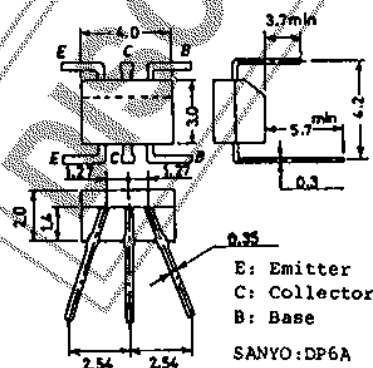
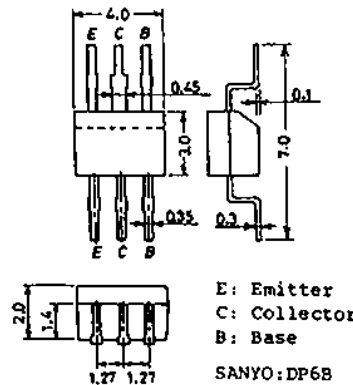
Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current	I _{CB0}			0.1	μA
Emitter Cutoff Current	I _{EB0}			0.1	μA
DC Current Gain	h _{FE}	160*		960*	
DC Current Gain Ratio	h _{FE} (small/large)	0.85	0.98		
Base to Emitter Voltage Drop	V _{BE} (large-small)		1.0	10	mV
Collector to Emitter Saturation Voltage	V _{CE(sat)}			0.5	V
Gain-Bandwidth Product	f _T		130		MHz
Output Capacitance	c _{ob}		1.6		pF

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*:The 2SC3067 is classified by h_{FE}(small) as follows:

160	F	320	280	G	560	480	H	960
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Case Outline 2029A
(unit:mm)**Case Outline 2030A**
(unit:mm)

The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced.

The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use; nor for any infringements of patents or other rights of third parties which may result from its use.

Specifications and information herein are subject to change without notice.

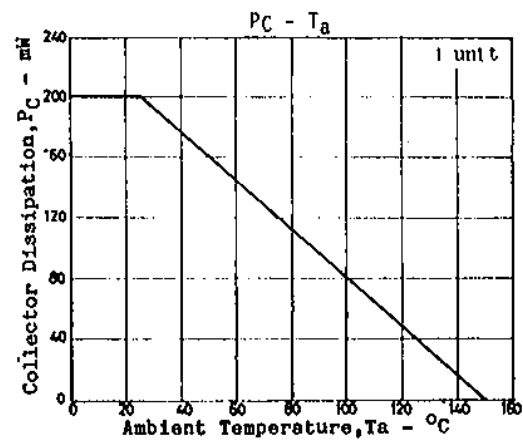
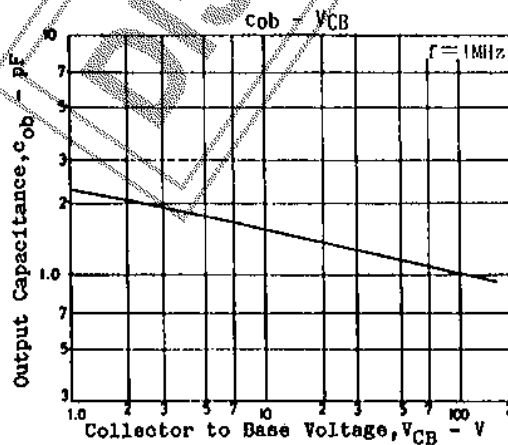
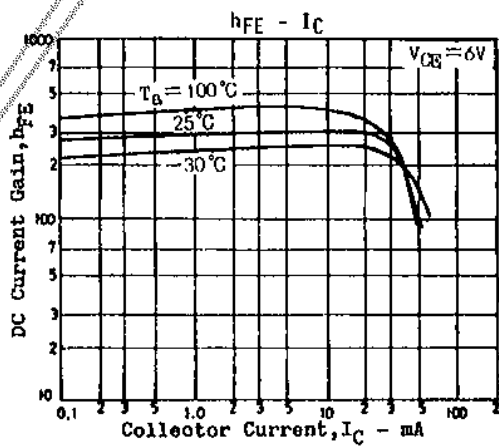
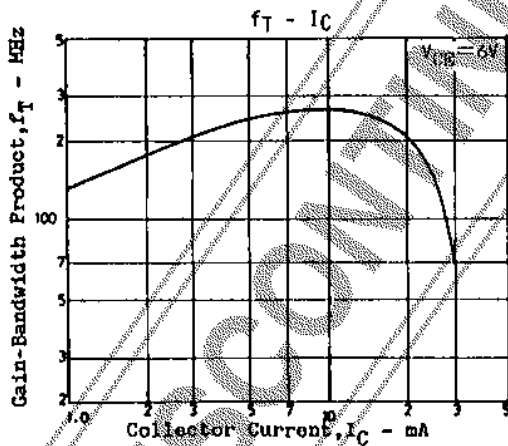
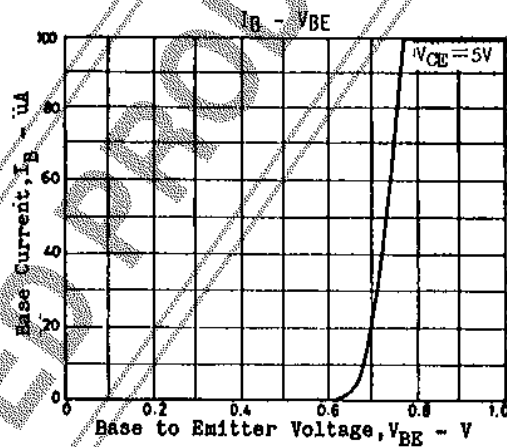
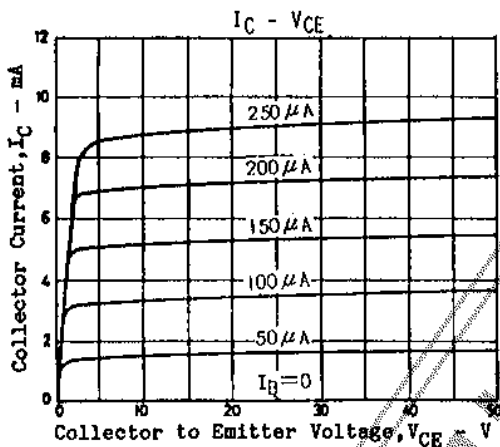
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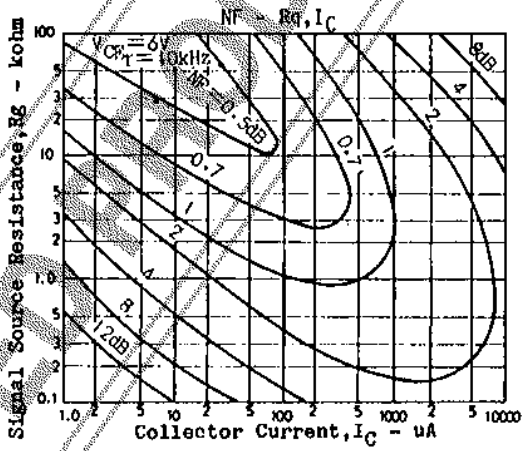
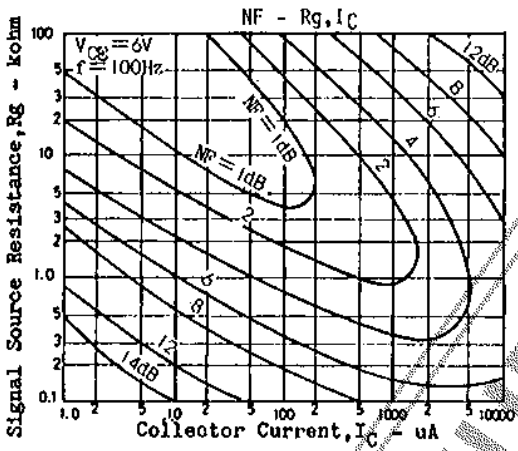
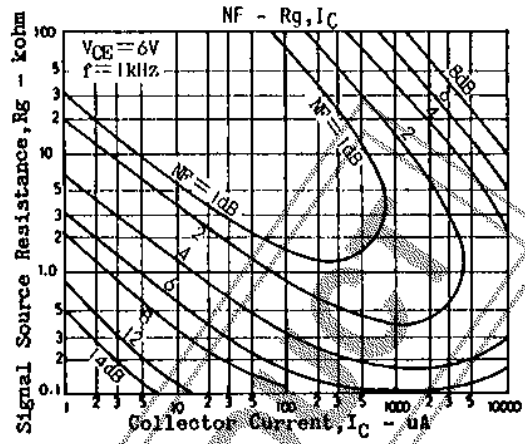
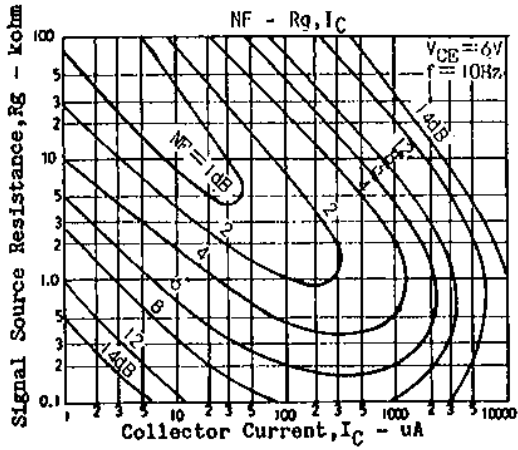
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2145KI, TS No.978-1/3

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			min	typ	max	unit
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	130			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	120			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Noise Level	$V_{NO(ave)}$	$V_{CC}=30V, I_C=1mA, R_g=56k\Omega, V_G=77dB/1kHz$			35	mV
Noise Peak Level	$V_{NO(peak)}$	$V_{CC}=30V, I_C=1mA, R_g=56k\Omega, V_G=77dB/1kHz$			200	mV





DISCONTINUED